

N-channel 600 V, 0.168  $\Omega$  typ., 18 A MDmesh II Plus™ low  $Q_g$   
Power MOSFET in D<sup>2</sup>PAK, I<sup>2</sup>PAK, TO-220 and TO-247 packages

Datasheet – production data

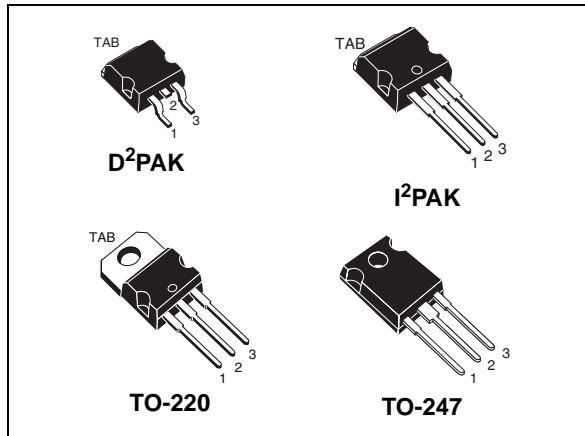
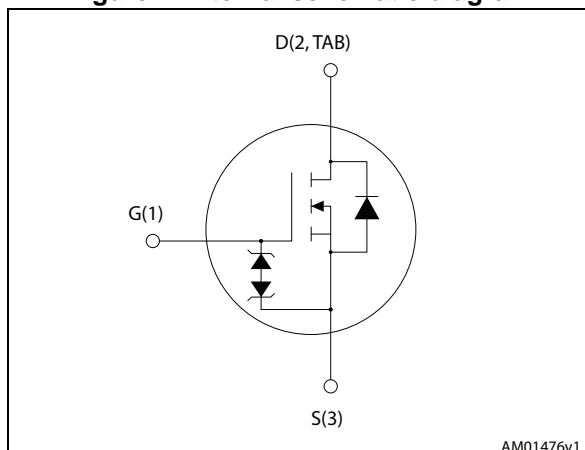


Figure 1. Internal schematic diagram



## Features

Order codes	$V_{DS} @ T_{Jmax}$	$R_{DS(on) max}$	$I_D$
STB24N60M2	650 V	0.19 $\Omega$	18 A
STI24N60M2			
STP24N60M2			
STW24N60M2			

- Extremely low gate charge
- Lower  $R_{DS(on)}$  x area vs previous generation
- Low gate input resistance
- 100% avalanche tested
- Zener-protected

## Applications

- Switching applications

## Description

These devices are N-channel Power MOSFETs developed using a new generation of MDmesh™ technology: MDmesh II Plus™ low  $Q_g$ . These revolutionary Power MOSFETs associate a vertical structure to the company's strip layout to yield one of the world's lowest on-resistance and gate charge. They are therefore suitable for the most demanding high efficiency converters.

Table 1. Device summary

Order codes	Marking	Package	Packaging
STB24N60M2	24N60M2	D <sup>2</sup> PAK	Tape and reel
STI24N60M2		I <sup>2</sup> PAK	Tube
STP24N60M2		TO-220	
STW24N60M2		TO-247	

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# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{GS}$	Gate-source voltage	$\pm 25$	V
$I_D$	Drain current (continuous) at $T_C = 25\text{ °C}$	18	A
$I_D$	Drain current (continuous) at $T_C = 100\text{ °C}$	12	A
$I_{DM}^{(1)}$	Drain current (pulsed)	72	A
$P_{TOT}$	Total dissipation at $T_C = 25\text{ °C}$	150	W
$dv/dt^{(2)}$	Peak diode recovery voltage slope	15	V/ns
$dv/dt^{(3)}$	MOSFET $dv/dt$ ruggedness	50	V/ns
$T_{stg}$	Storage temperature	- 55 to 150	°C
$T_j$	Max. operating junction temperature		

1. Pulse width limited by safe operating area.
2.  $I_{SD} \leq 18\text{ A}$ ,  $di/dt \leq 400\text{ A}/\mu\text{s}$ ;  $V_{DS\text{ peak}} < V_{(BR)DSS}$ ;  $V_{DD}=400\text{ V}$ .
3.  $V_{DS} \leq 480\text{ V}$

**Table 3. Thermal data**

Symbol	Parameter	Value				Unit
		D <sup>2</sup> PAK	I <sup>2</sup> PAK	TO-220	TO-247	
$R_{thj-case}$	Thermal resistance junction-case max	0.83				°C/W
$R_{thj-pcb}$	Thermal resistance junction-pcb max <sup>(1)</sup>	30				°C/W
$R_{thj-amb}$	Thermal resistance junction-ambient max		62.5	50		°C/W

1. When mounted on 1 inch<sup>2</sup> FR-4, 2 Oz copper board

**Table 4. Avalanche characteristics**

Symbol	Parameter	Value	Unit
$I_{AR}$	Avalanche current, repetitive or not repetitive (pulse width limited by $T_{jmax}$ )	3.5	A
$E_{AS}$	Single pulse avalanche energy (starting $T_j=25\text{ °C}$ , $I_D = I_{AR}$ ; $V_{DD}=50$ )	180	mJ

## 2 Electrical characteristics

( $T_C = 25\text{ °C}$  unless otherwise specified)

**Table 5. On /off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}$ , $V_{GS} = 0$	600			V
$I_{DSS}$	Zero gate voltage drain current ( $V_{GS} = 0$ )	$V_{DS} = 600\text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 600\text{ V}$ , $T_C = 125\text{ °C}$			100	$\mu\text{A}$
$I_{GSS}$	Gate-body leakage current ( $V_{DS} = 0$ )	$V_{GS} = \pm 25\text{ V}$			$\pm 10$	$\mu\text{A}$
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$	2	3	4	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$ , $I_D = 9\text{ A}$		0.168	0.19	$\Omega$

**Table 6. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 100\text{ V}$ , $f = 1\text{ MHz}$ , $V_{GS} = 0$	-	1060	-	pF
$C_{oss}$	Output capacitance		-	55	-	pF
$C_{rss}$	Reverse transfer capacitance		-	2.2	-	pF
$C_{oss\text{ eq.}}^{(1)}$	Equivalent output capacitance	$V_{DS} = 0\text{ to }480\text{ V}$ , $V_{GS} = 0$	-	258	-	pF
$R_G$	Intrinsic gate resistance	$f = 1\text{ MHz}$ , $I_D = 0$	-	7	-	$\Omega$
$Q_g$	Total gate charge	$V_{DD} = 480\text{ V}$ , $I_D = 18\text{ A}$ , $V_{GS} = 10\text{ V}$ (see <a href="#">Figure 17</a> )	-	29	-	nC
$Q_{gs}$	Gate-source charge		-	6	-	nC
$Q_{gd}$	Gate-drain charge		-	12	-	nC

1.  $C_{oss\text{ eq.}}$  is defined as a constant equivalent capacitance giving the same charging time as  $C_{oss}$  when  $V_{DS}$  increases from 0 to 80%  $V_{DSS}$

**Table 7. Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 300\text{ V}$ , $I_D = 9\text{ A}$ , $R_G = 4.7\text{ }\Omega$ , $V_{GS} = 10\text{ V}$ (see <a href="#">Figure 16</a> and <a href="#">21</a> )	-	14	-	ns
$t_r$	Rise time		-	9	-	ns
$t_{d(off)}$	Turn-off delay time		-	60	-	ns
$t_f$	Fall time		-	15	-	ns

Table 8. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current		-		18	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		72	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 18\text{ A}$ , $V_{GS} = 0$	-		1.6	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 18\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 60\text{ V}$ (see <a href="#">Figure 18</a> )	-	332		ns
$Q_{rr}$	Reverse recovery charge		-	4		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current		-	24		A
$t_{rr}$	Reverse recovery time	$I_{SD} = 18\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 60\text{ V}$ , $T_j = 150\text{ }^\circ\text{C}$ (see <a href="#">Figure 18</a> )	-	450		ns
$Q_{rr}$	Reverse recovery charge		-	5.5		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current		-	25		A

1. Pulse width limited by safe operating area.
2. Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

## 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for D<sup>2</sup>PAK, I<sup>2</sup>PAK and TO-220 Figure 3. Thermal impedance D<sup>2</sup>PAK, I<sup>2</sup>PAK and TO-220

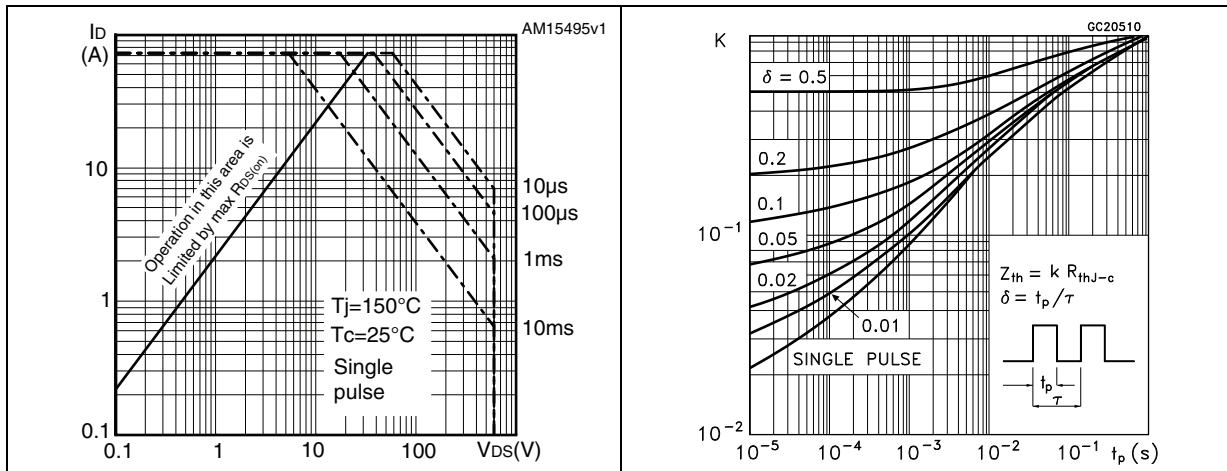


Figure 4. Safe operating area for TO-247

Figure 5. Thermal impedance for TO-247

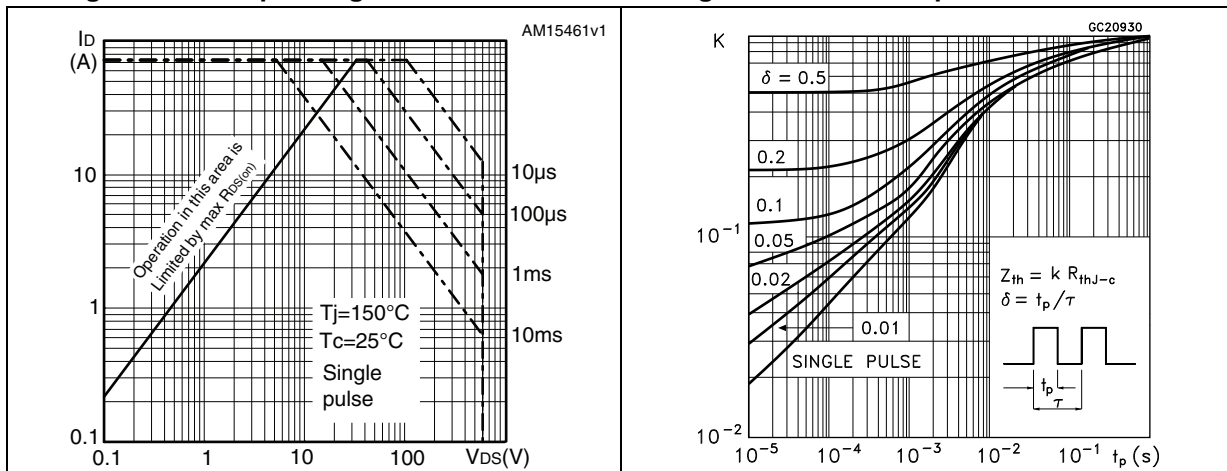


Figure 6. Output characteristics

Figure 7. Transfer characteristics

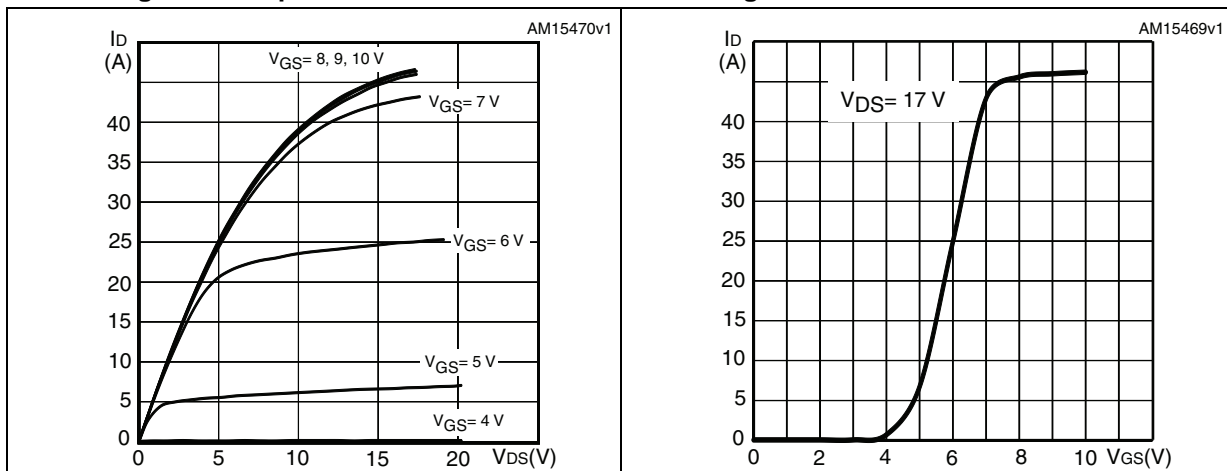


Figure 8. Gate charge vs gate-source voltage

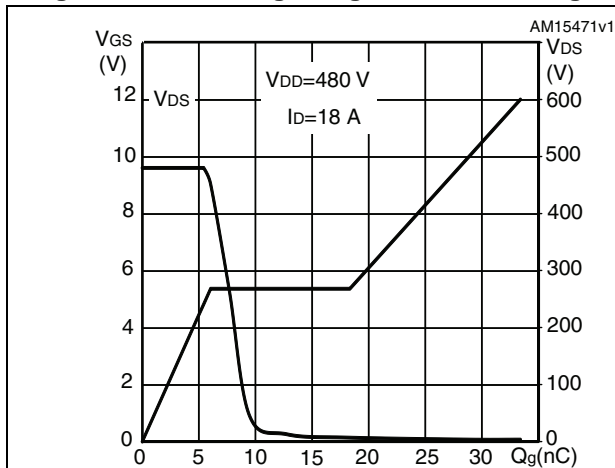


Figure 9. Static drain-source on-resistance

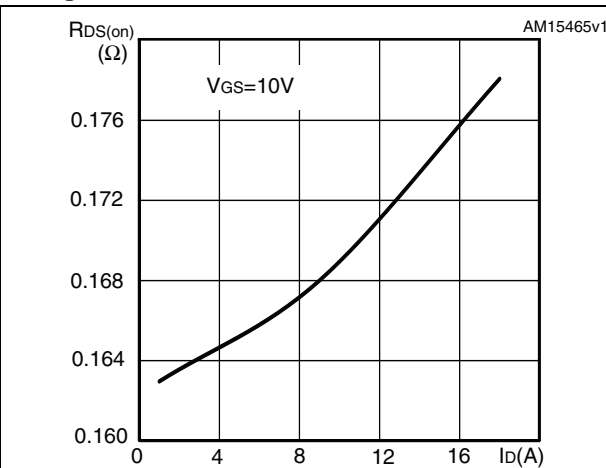


Figure 10. Capacitance variations

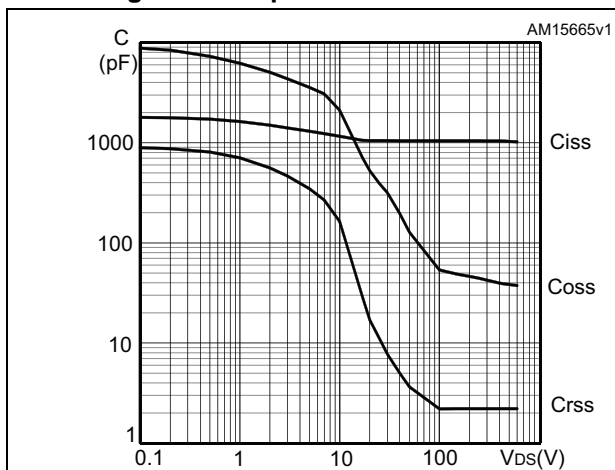


Figure 11. Output capacitance stored energy

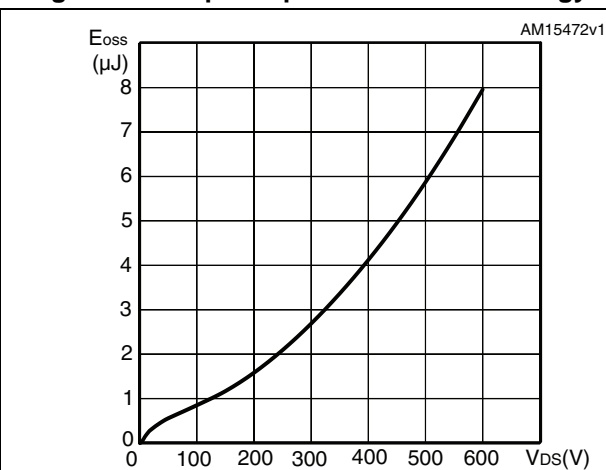


Figure 12. Normalized gate threshold voltage vs temperature

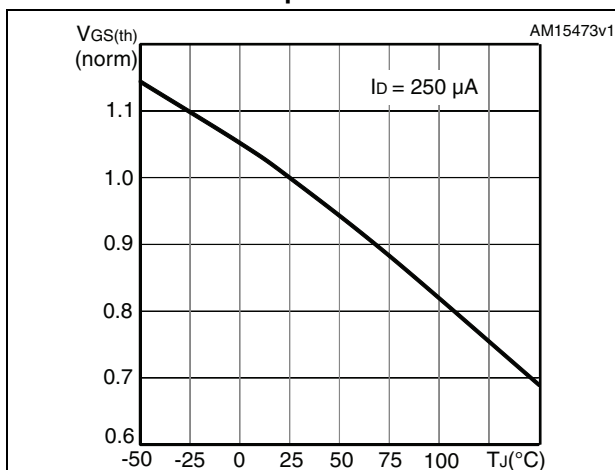


Figure 13. Normalized on-resistance vs temperature

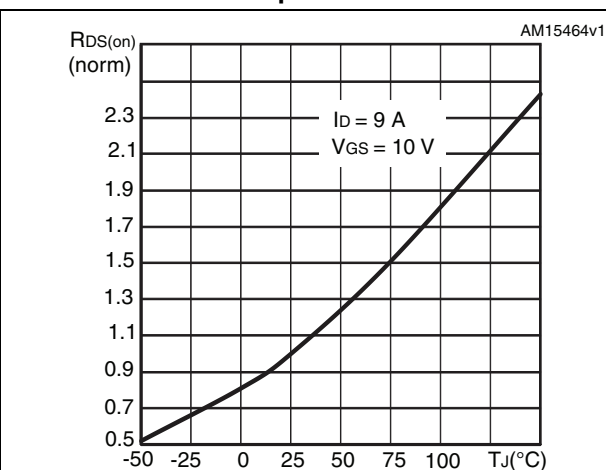


Figure 14. Source-drain diode forward characteristics

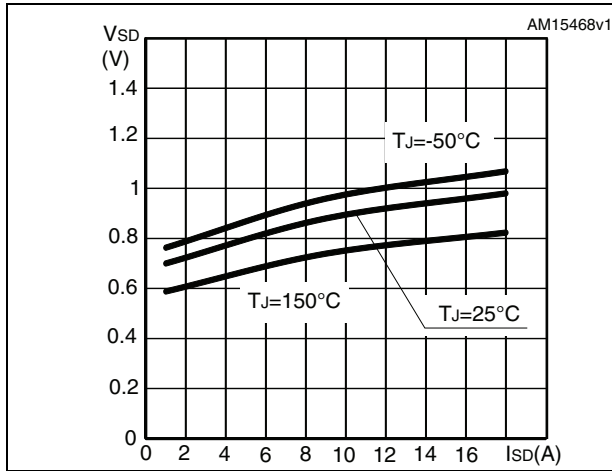
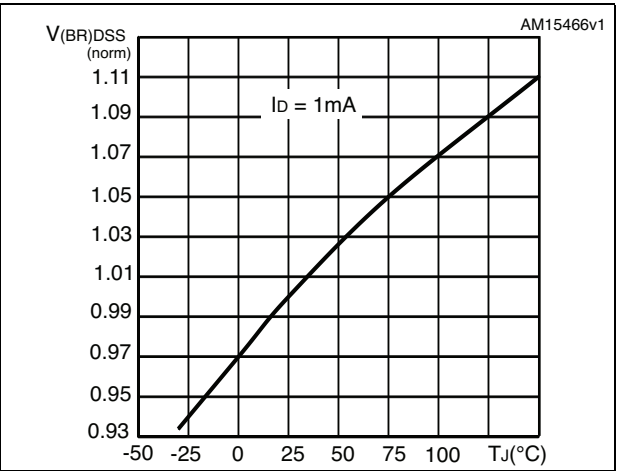


Figure 15. Normalized  $V_{(BR)DSS}$  vs temperature





### 3 Test circuits

Figure 16. Switching times test circuit for resistive load



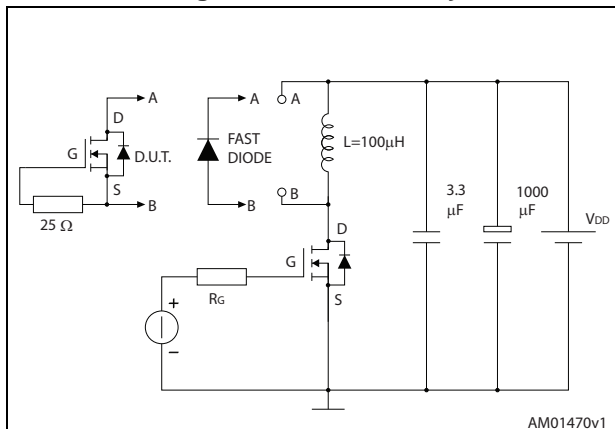
AM01468v1

Figure 17. Gate charge test circuit



AM01469v1

Figure 18. Test circuit for inductive load switching and diode recovery times



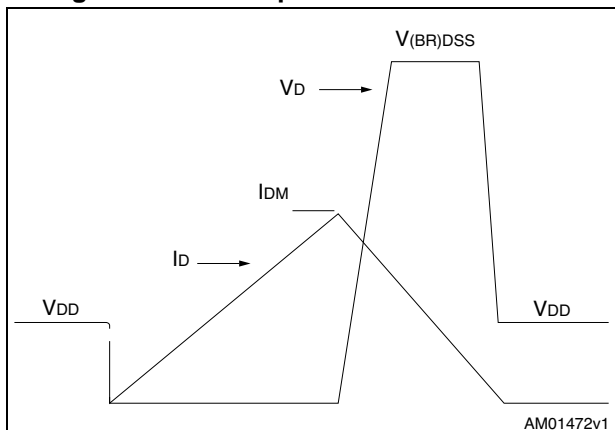
AM01470v1

Figure 19. Unclamped inductive load test circuit



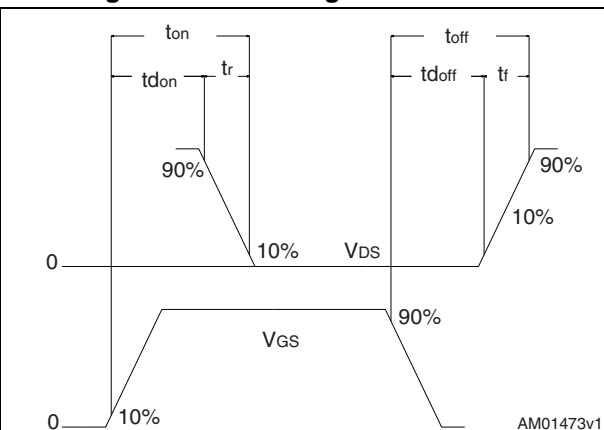
AM01471v1

Figure 20. Unclamped inductive waveform



AM01472v1

Figure 21. Switching time waveform



AM01473v1

## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK<sup>®</sup> is an ST trademark.

Figure 22. D<sup>2</sup>PAK (TO-263) drawing

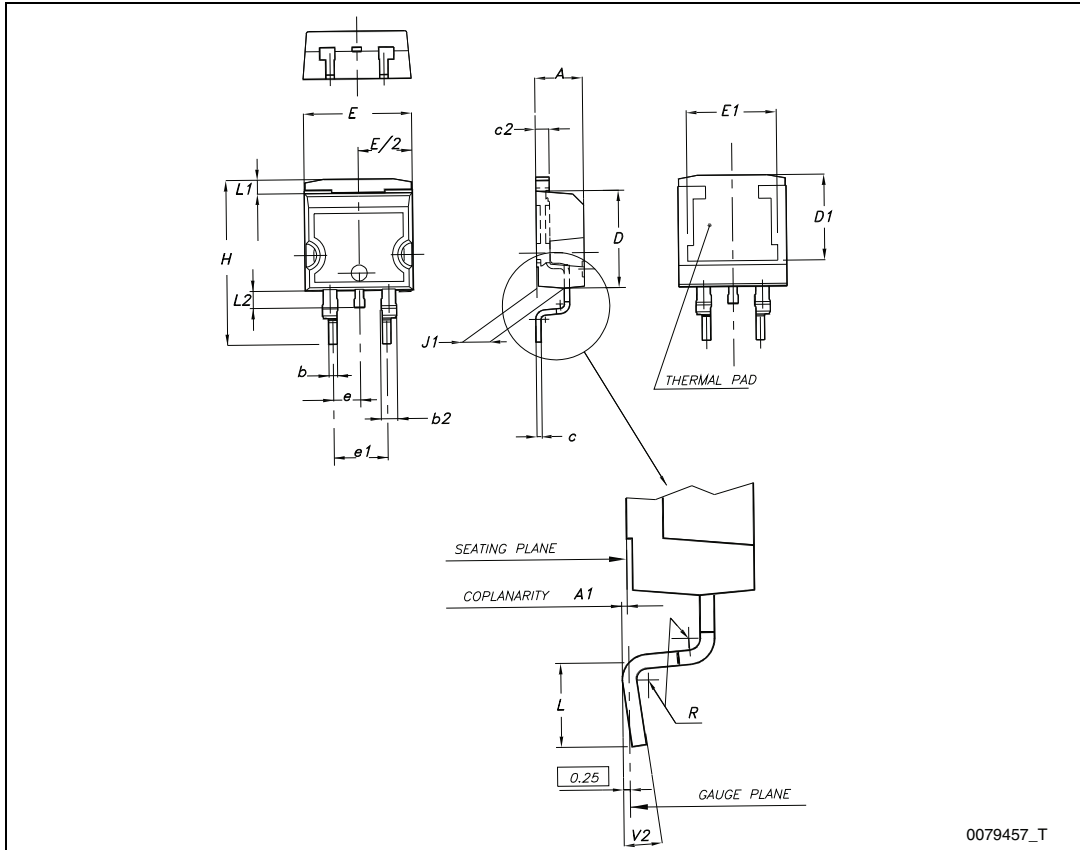


Table 9. D<sup>2</sup>PAK (TO-263) mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50		
E	10		10.40
E1	8.50		
e		2.54	
e1	4.88		5.28
H	15		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.4	
V2	0°		8°

Figure 23. D<sup>2</sup>PAK footprint<sup>(a)</sup>

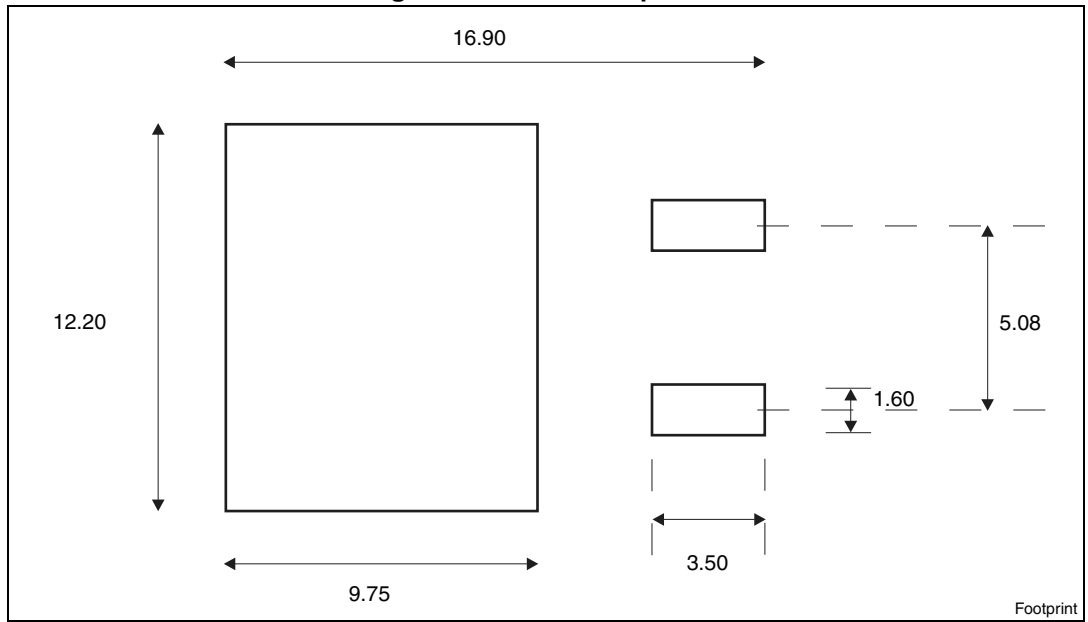
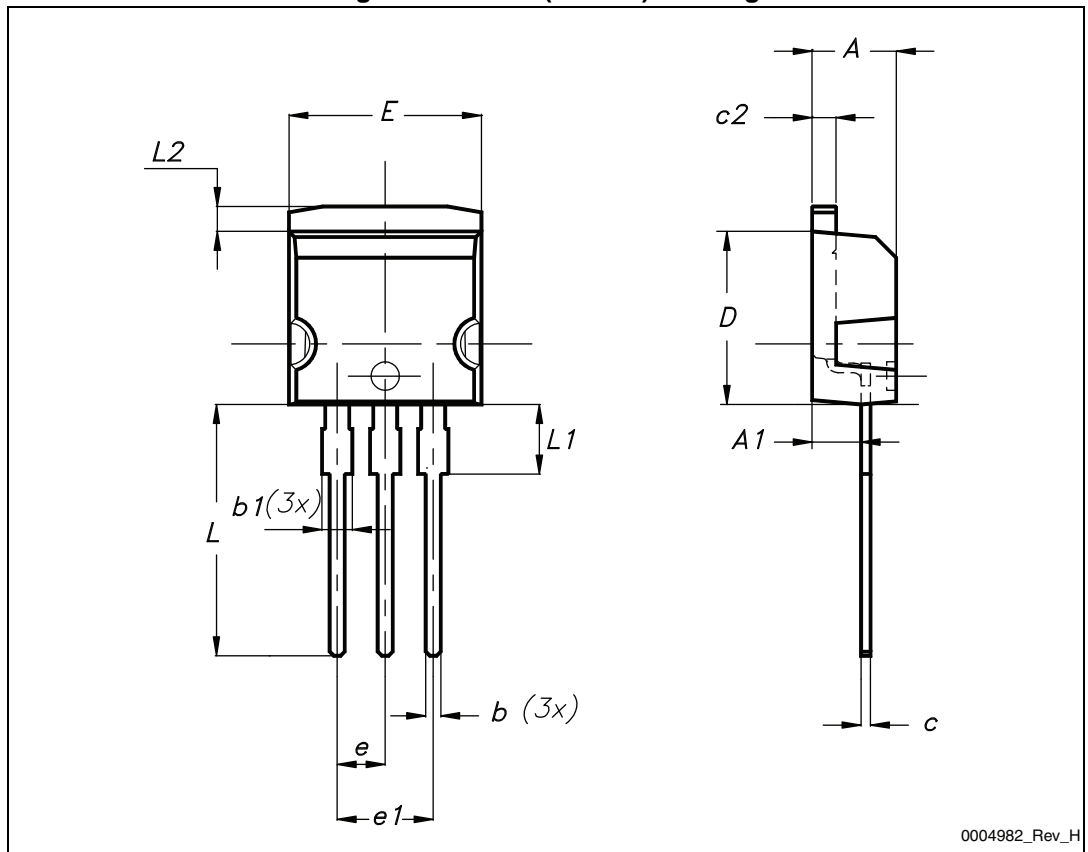


Figure 24. I<sup>2</sup>PAK (TO-262) drawing

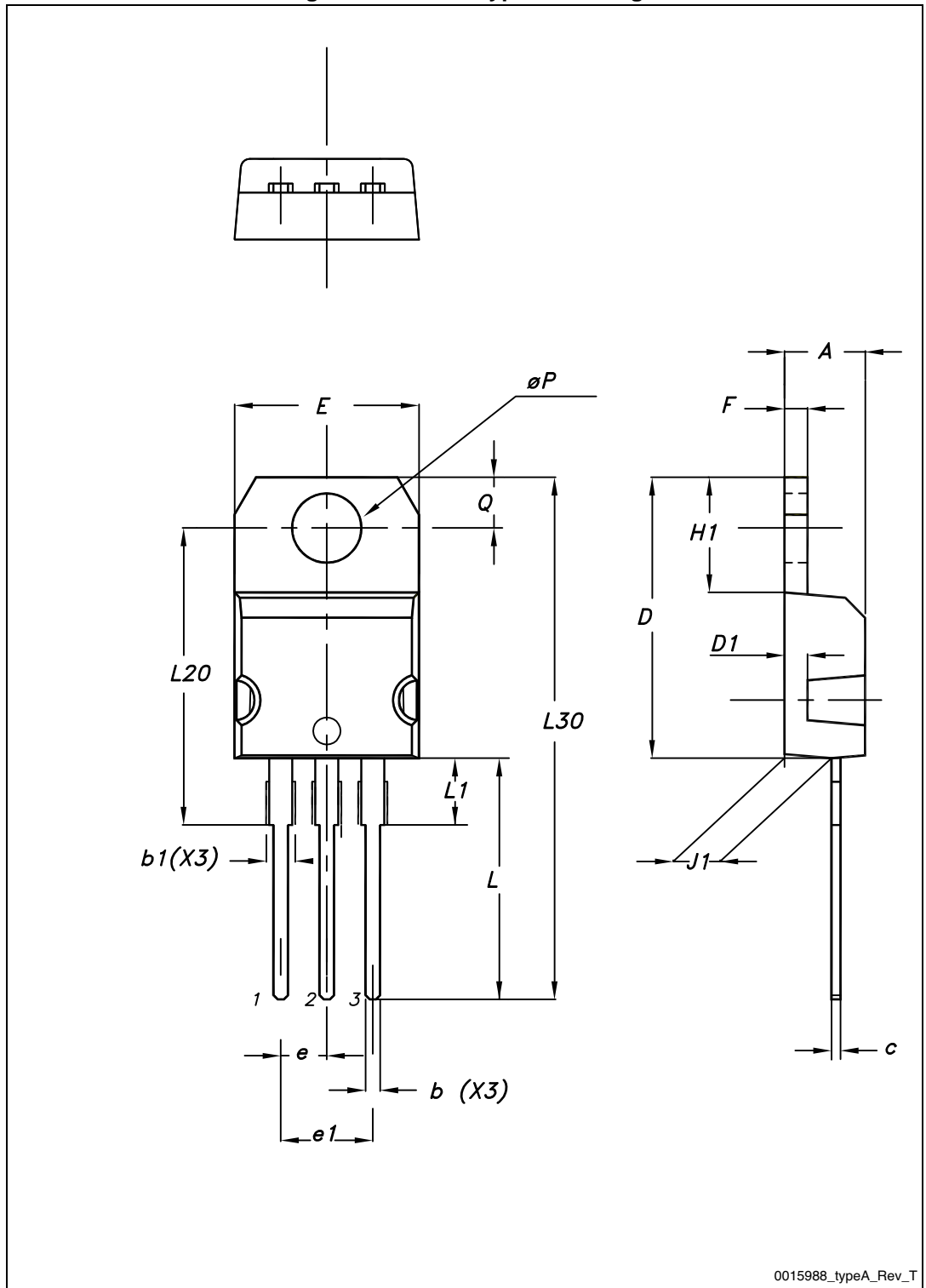


a. All dimension are in millimeters

Table 10. I<sup>2</sup>PAK (TO-262) mechanical data

DIM.	mm.		
	min.	typ	max.
A	4.40		4.60
A1	2.40		2.72
b	0.61		0.88
b1	1.14		1.70
c	0.49		0.70
c2	1.23		1.32
D	8.95		9.35
e	2.40		2.70
e1	4.95		5.15
E	10		10.40
L	13		14
L1	3.50		3.93
L2	1.27		1.40

Figure 25. TO-220 type A drawing



0015988\_typeA\_Rev\_T

Table 11. TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
∅P	3.75		3.85
Q	2.65		2.95

Figure 26. TO-247 drawing

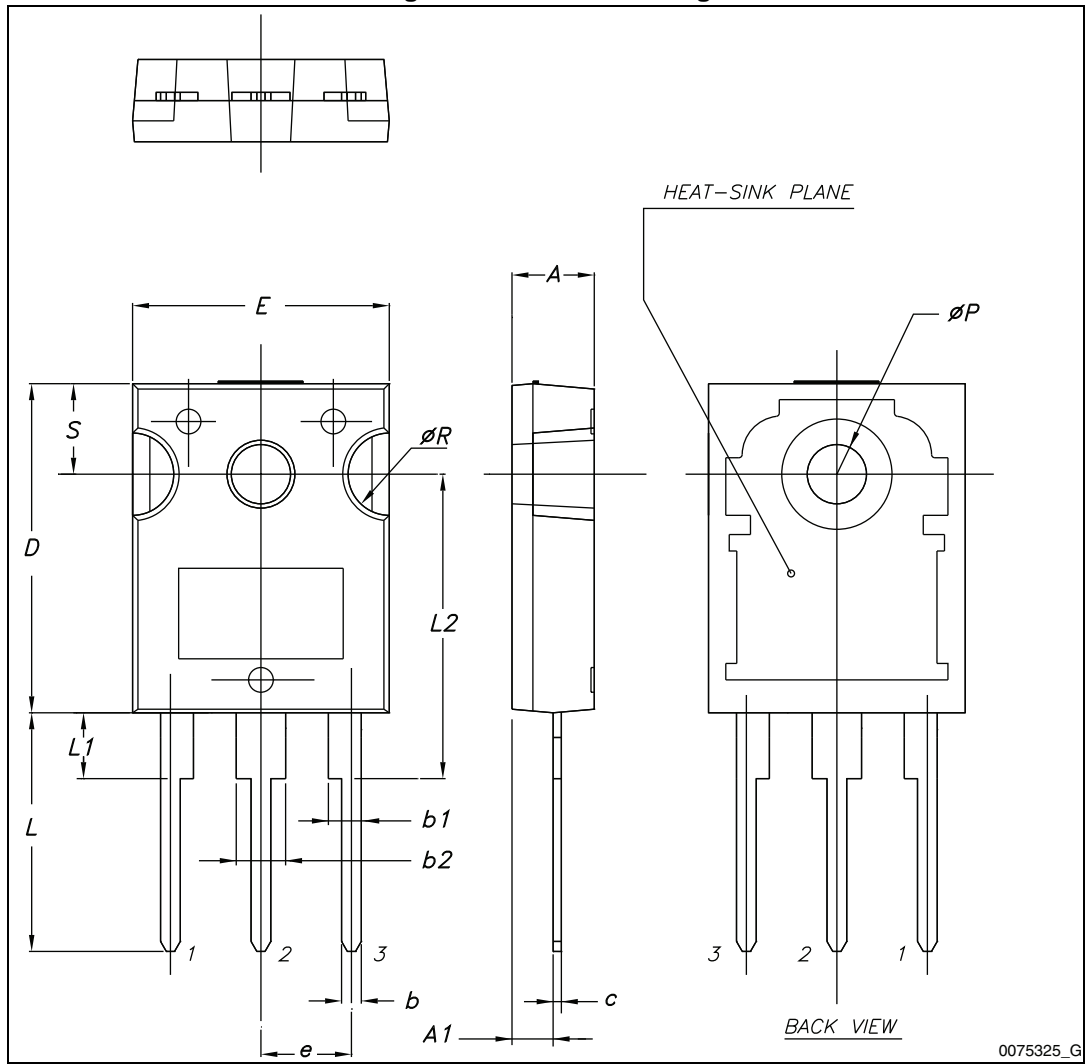




Table 12. TO-247 mechanical data

Dim.	mm.		
	Min.	Typ.	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e	5.30	5.45	5.60
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
ØP	3.55		3.65
ØR	4.50		5.50
S	5.30	5.50	5.70

# 5 Packaging mechanical data

Figure 27. Tape

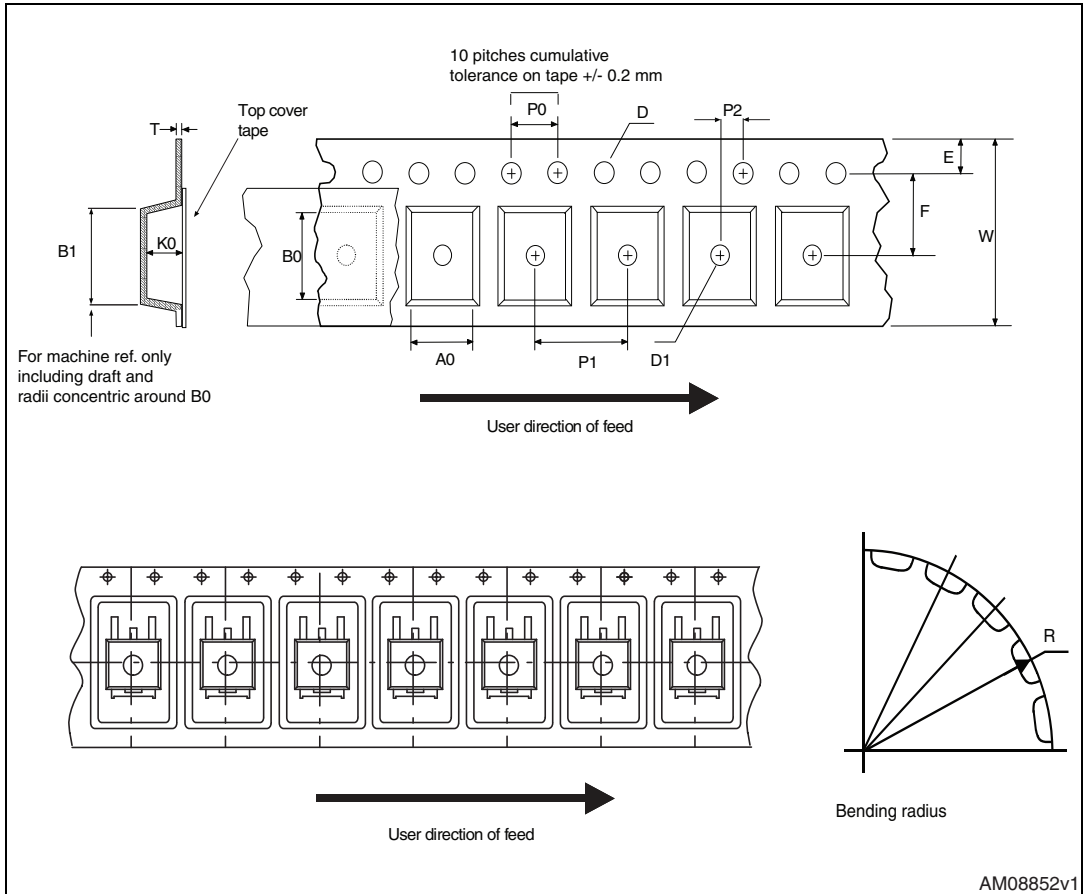


Figure 28. Reel

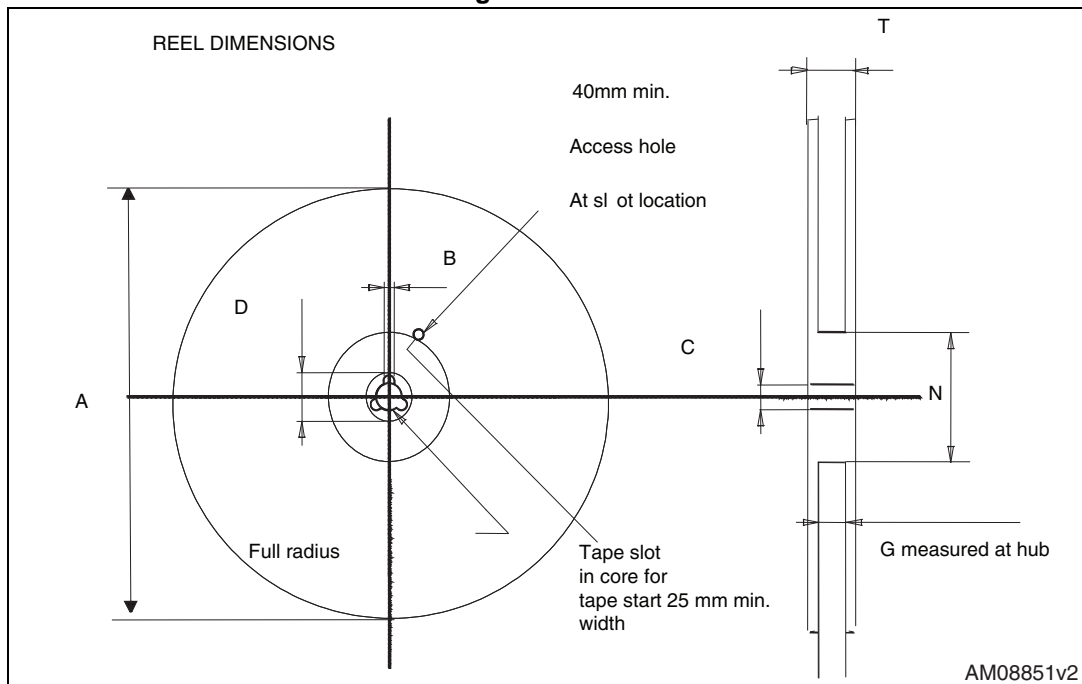


Table 13. D<sup>2</sup>PAK (TO-263) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1	Base qty		1000
P2	1.9	2.1	Bulk qty		1000
R	50				
T	0.25	0.35			
W	23.7	24.3			

## 6 Revision history

Table 14. Document revision history

Date	Revision	Changes
10-Dec-2012	1	First release.
20-Dec-2012	2	Added MOSFET dv/dt ruggedness in <a href="#">Table 2: Absolute maximum ratings</a> .
14-Jan-2013	3	Modified: <a href="#">Figure 16</a> , <a href="#">17</a> , <a href="#">18</a> and <a href="#">17</a>
28-May-2013	4	<ul style="list-style-type: none"><li>– Minor text changes</li><li>– Updated: <a href="#">Table 7</a></li><li>– Updated: <a href="#">Table 11</a> and <a href="#">Figure 25</a></li></ul>
28-Feb-2014	5	<ul style="list-style-type: none"><li>– Minor text changes</li><li>– Modified: title of <a href="#">Figure 15</a>.</li><li>– Modified: <a href="#">Figure 16</a>, <a href="#">17</a>, <a href="#">18</a> and <a href="#">19</a></li></ul>

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